

**PXT8050 TRANSISTOR (NPN)**

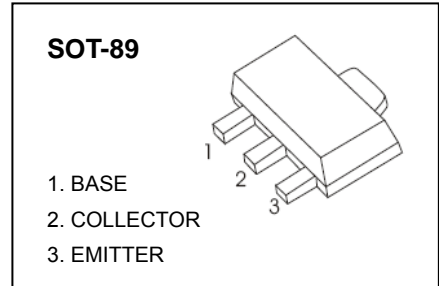
**FEATURES**

Compliment to PXT8550

**MARKING: Y1**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1.5	A
P <sub>C</sub>	Collector Power dissipation	0.5	W
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	250	°C/W
T <sub>J</sub>	Storage Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C



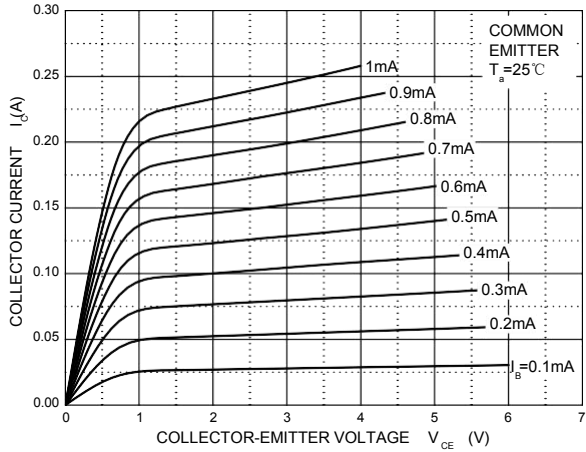
**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =0.1mA, I <sub>B</sub> =0	25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =20V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	120		400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =800mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			1.2	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA			1	V
Base-emitter positive favor voltage	V <sub>BEF</sub>	I <sub>B</sub> =1A			1.55	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA, f=30MHz	100			MHz
output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			15	pF

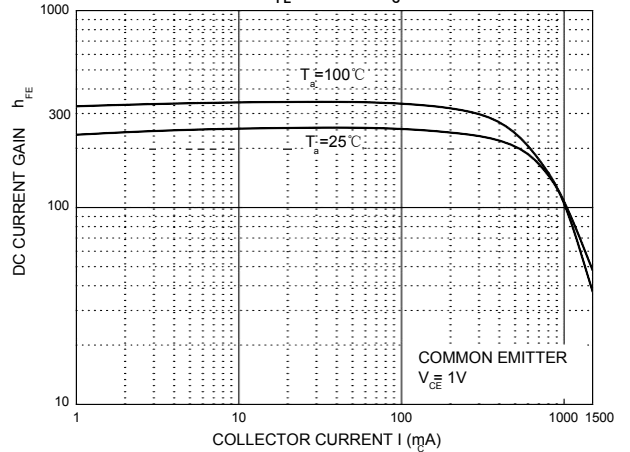
**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	C	D	D1	D2
Range	120-200	160-300	200-350	300-400

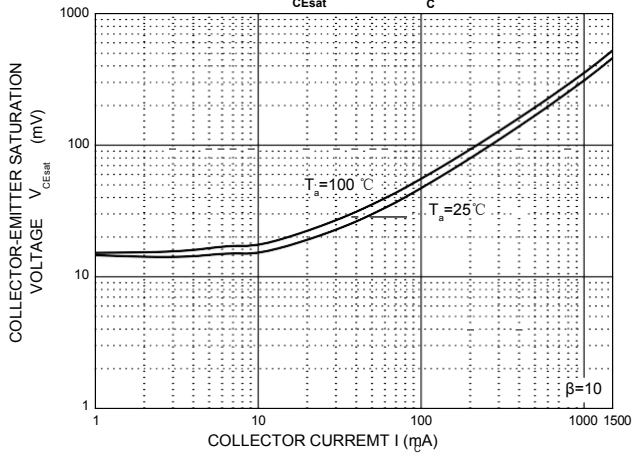
Static Characteristic



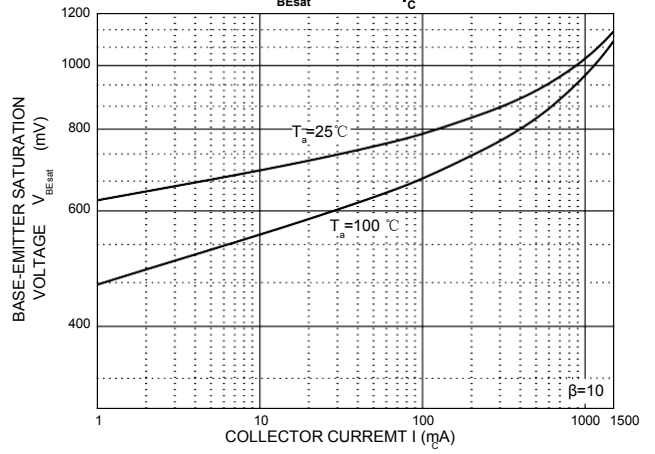
$h_{FE}$  —  $I_c$



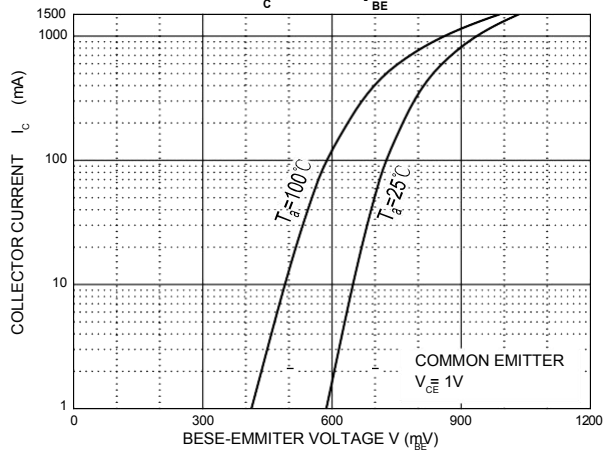
$V_{CEsat}$  —  $I_c$



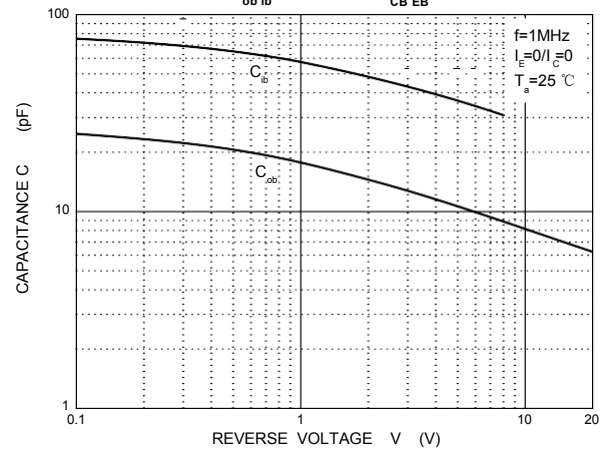
$V_{BEsat}$  —  $I_c$



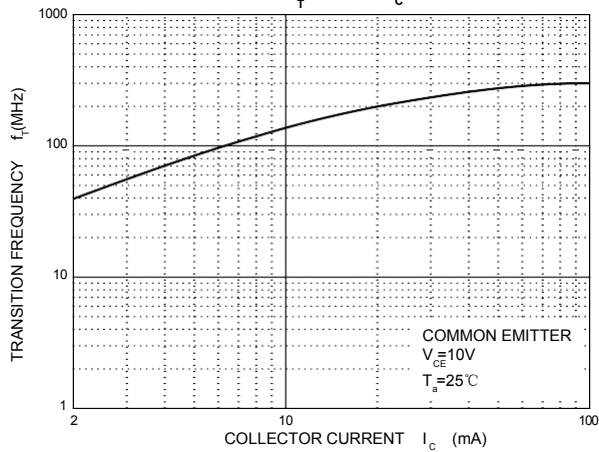
$I_c$  —  $V_{BE}$



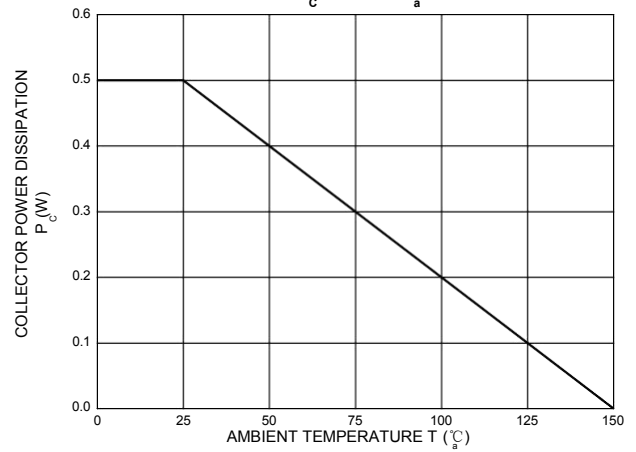
$C_{ob}/C_{ib}$  —  $V_{CE}/V_{EB}$



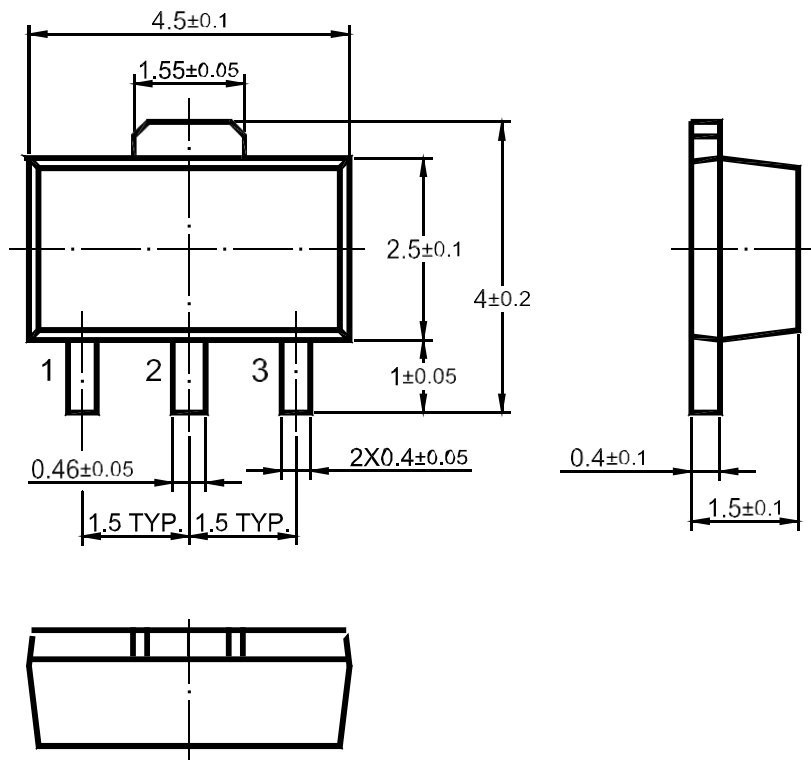
$f_T$  —  $I_c$



$P_c$  —  $T_a$



SOT-89 PACKAGE OUTLINE



Dimensions in mm

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